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**Overview**

Use the remainder of this page for your abstract text. This must be in Times New Roman font that is at least 10 pt. Either single or double column format is acceptable. You are encouraged to use headings (in **bold**) for different sections such as: **Introduction**, **Experimental Process**, **Device Results**, and **Significance** or **Conclusion**. The use of these (or any other) headings is not required, but may be used to bring greater clarity to your abstract. Remember that the abstract *must clearly communicate the new and significant results that have been obtained*. What makes the reported work important? Why are these results significant compared to previous related work?

**Margins**

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**Figures Page**

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* Figures and captions *must* be kept to within the 1” (2.5 cm) page margins.
* All Figures should have a corresponding caption.
* Font for the Figure captions *must* be kept to Times New Roman 10 pt.
* All Figures should be given a number (*e.g.,* Fig. 1, Fig. 2, etc.) and referred to at some point in the Text (on this page).
* Figures with multiple parts should have each part distinctly labeled with ‘a)’, ‘b)’, ‘c)’, etc.

**References**

All references should be *on the bottom of this page*. It is recommended that the references follow the format used for *IEEE Electron Device Letters* (<http://eds.ieee.org/edl.html>), but other formats are accepted, including more concise versions that use *et al.*, only give the first page for an article, and so on. The font for the references must be Times New Roman with at least 9 pt. size and they may also be assembled in a column-like fashion as shown below to save space. Be sure that you do not change the page margins to try and create more space for references! Also, references should not be placed on the Figures page.

**Submission**

For submission, the abstract should be saved as a PDF file (or converted to PDF in some fashion). Please do not insert page numbers or any other text in the footer or header of the file.

[1] A. D. Franklin *et al.*, *IEEE-EDL,* vol. 33, p. 17, (2012). [2] R. Yan *et al.*, *Nano Lett.*, vol. 15, p. 5791, (2015).

[3] R. Salas *et al.*, *Appl. Phys. Lett.*, vol. 106, p. 081103, (2015). [4] S. -J. Han *et al.*, *IEDM Tech. Dig.*, p. 2.2.1, (2011).

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| **Fig. 1** Schematic epitaxial stack of the modulation-doped double heterostructure. | **Fig. 2** Equilibrium energy band diagram and calculated 2DEG charge distribution. | **Fig. 3** AFM image of the surface. The RMS value is 0.57 nm. |
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| **Fig. 4** XRD of the modulation doped structure | **Fig. 5** Temperature-dependence of charge densities and electron mobility measured using a Van der Pauw configuration. | **Fig. 6** Capacitance-voltage profile measured at 1 MHz |
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| **Fig. 7** Charge profile extracted from the CV measurement. The channel sits at 31 nm from the top surface.  | **Fig. 8** Output characteristics of the device with LSD=3.3 µm, LG=0.7 µm. The gate bias was scanned from 2 V to -10 V with a step of 1 V.  | **Fig. 9** Tranfer characteristics of the device with LSD=3.3 µm, LG=0.7 µm. The drain bias was kept at 10 V.  |

These figures are taken from Y. Zhang, Z. Xia, C. Joishi, and S. Rajan, “Design and Demonstration of (Al,Ga)2O3/Ga2O3 Double Heterostructure Field Effect Transistor (DHFET),” 77th Annual Device Research Conference (DRC), Ann Arbor, MI, 2019.